

# **INDIUM** Arsenide Powder

Indium arsenide, InAs, or indium monoarsenide, is a semiconductor composed of indium and arsenic. It has the appearance of grey cubic crystals with a melting point of 942 °C. Indium arsenide is popular for its narrow energy and high electron mobility. Indium arsenide is also used for making of diode lasers. Indium arsenide is similar to gallium arsenide and is a direct bandgap material. Indium arsenide is sometimes used together with indium phosphide. Alloyed with gallium arsenide it forms indium gallium arsenide - a material with band gap dependent on In/Ga ratio, a method principally similar to alloying indium nitride with gallium nitride to yield indium gallium nitride.

InAs

106097-59-0

## **Quick** Facts

Product Indium Arsenide Powder Stock No NS6130-12-000352 106097-59-0 CAS

Color Grey Powder

### **TECHNICAL** Specification

40-50µm Purity 99.99% 189.740g/mol Molecular Weight: Density 5.67 g/cm<sup>3</sup> Melting Point 942°C



**PURITY** 

#### **APPLICATIONS**

- Diode lasers are also made using indium arsenide
- It is used as a terahertz radiation source
- Indium arsenide and gallium arsenide are similar and it is a direct bandgap material.
- It is possible to form quantum dots in a monolayer of indium arsenide on gallium arsenide or indium phosphide

#### **Packing Sizes:**

25Gms, 50Gms, 100Gms, 500Gms & Bulk Orders

**APS** 

40-50µm













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ISO 9001:2015 CERTIFIED COMPANY

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